

FIG. 1

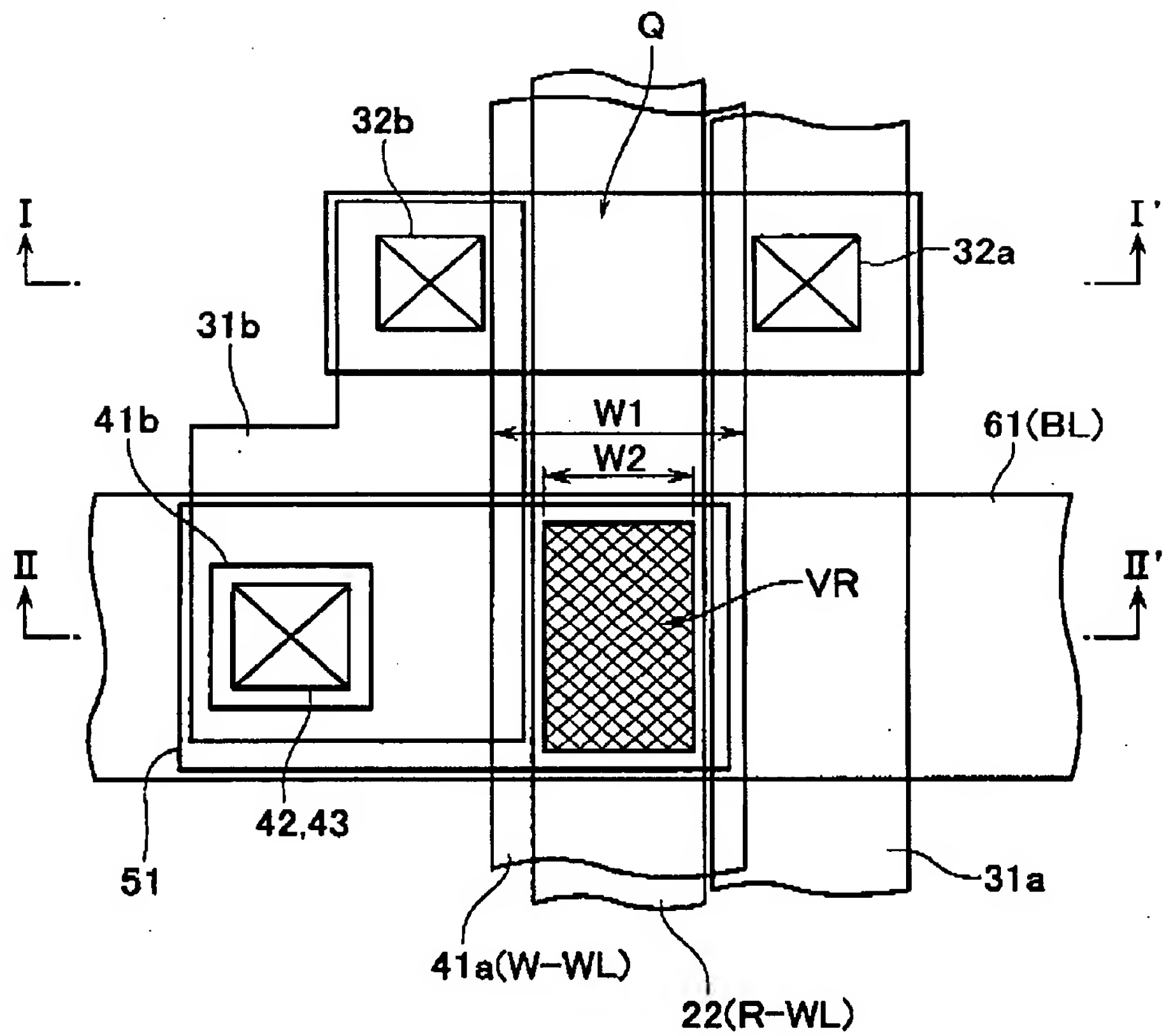


FIG. 2A

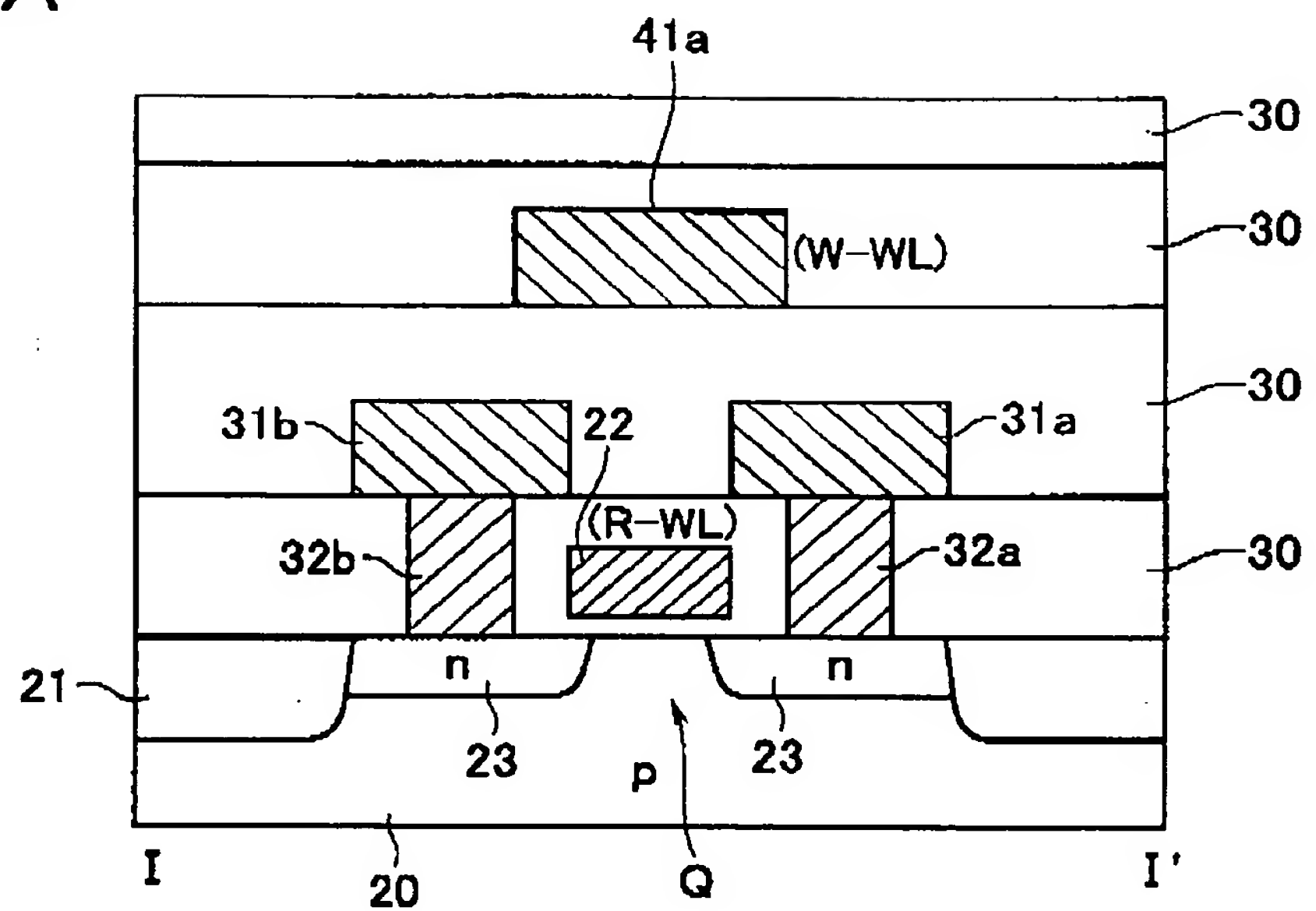


FIG. 2B

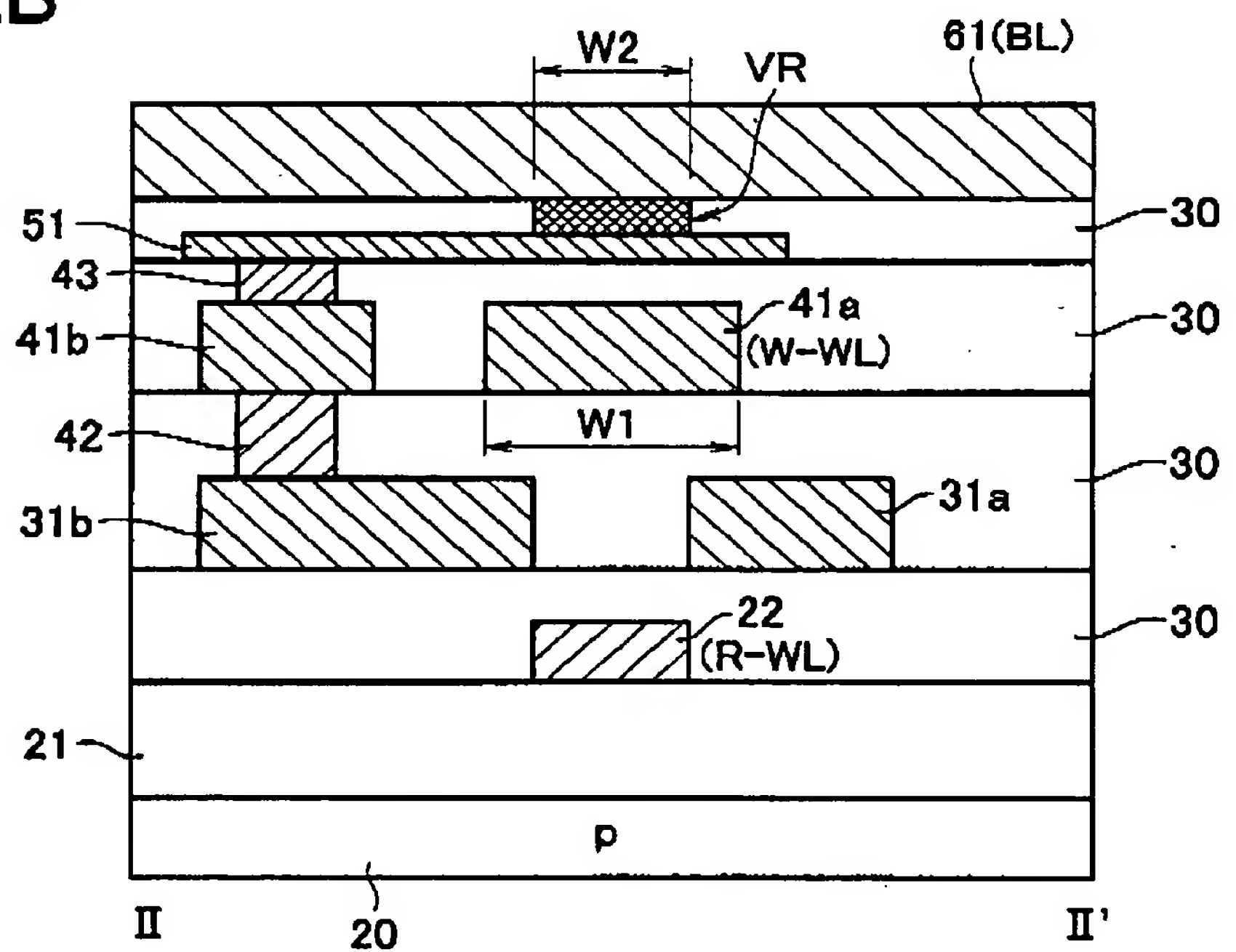
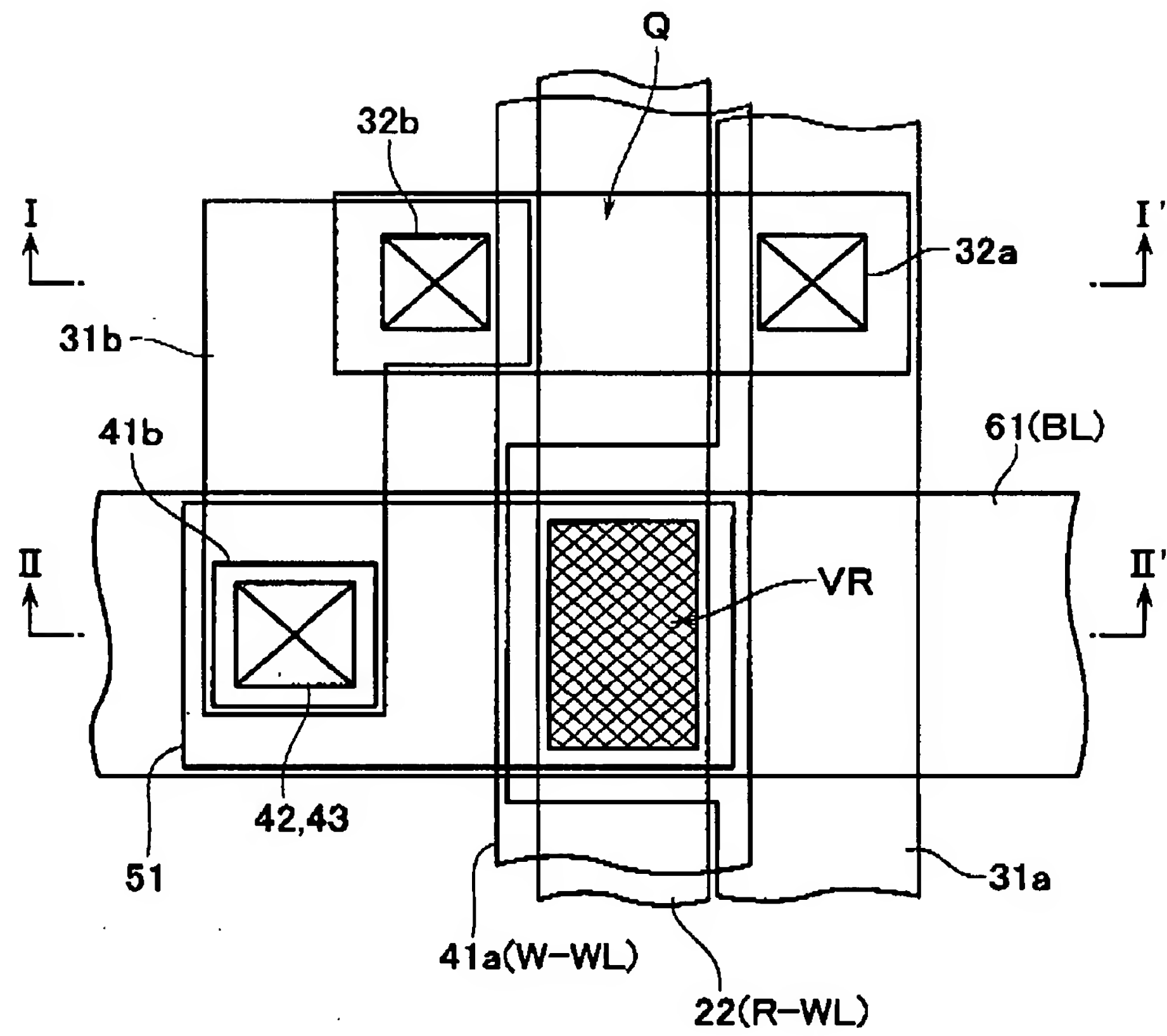


FIG. 3



A cross-sectional view of a semiconductor device. The substrate 20 is shown with p-type regions 23 and n-type regions 22. A gate stack 30 is formed on top, including a gate oxide 31a, 31b, 32a, 32b, and a gate electrode 41a. The gate electrode is connected to a word line (W-WL) and a read word line (R-WL). The device is labeled with I, I', Q, and 21.

[illegible]

FIG. 5

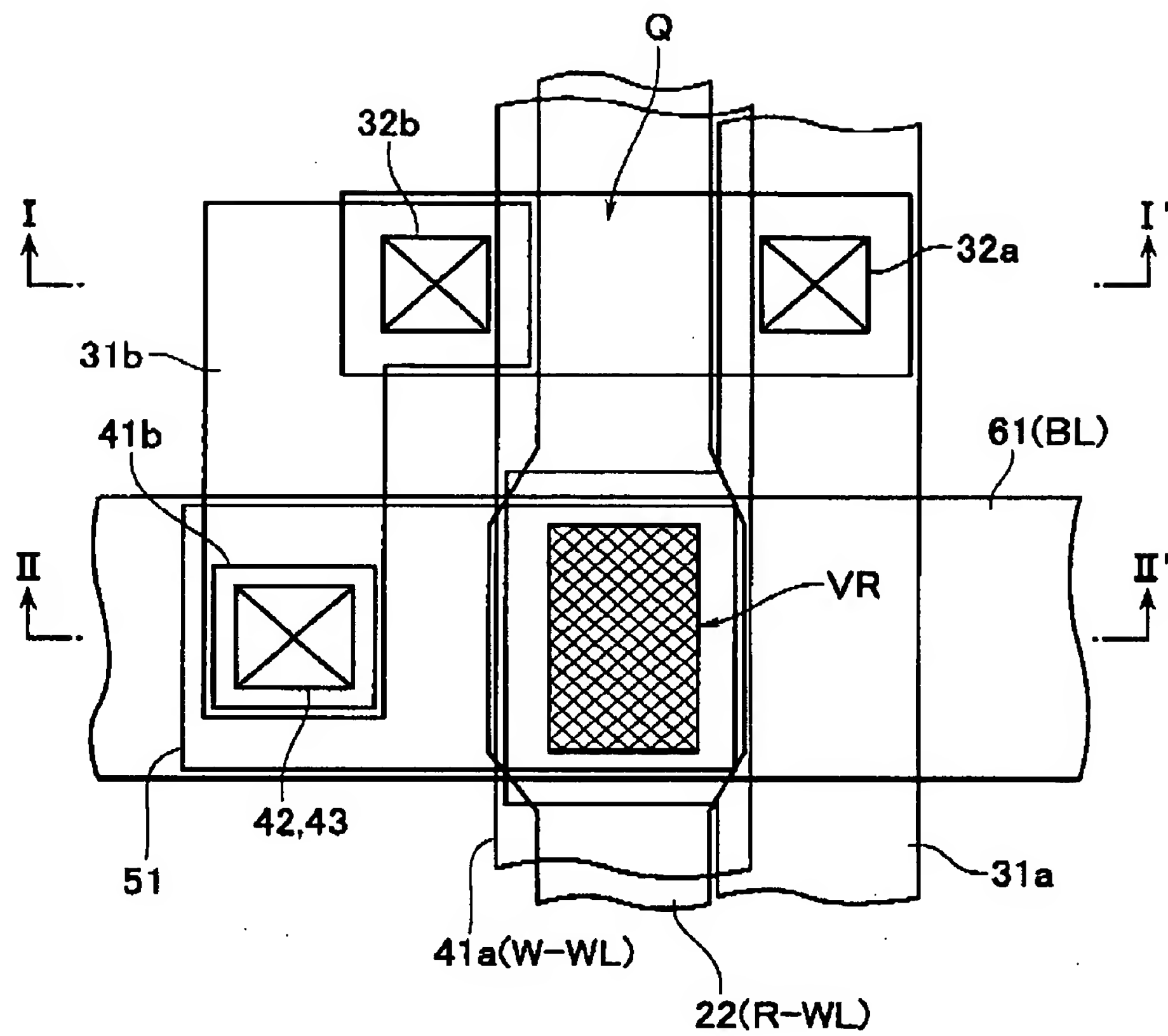


FIG. 6A

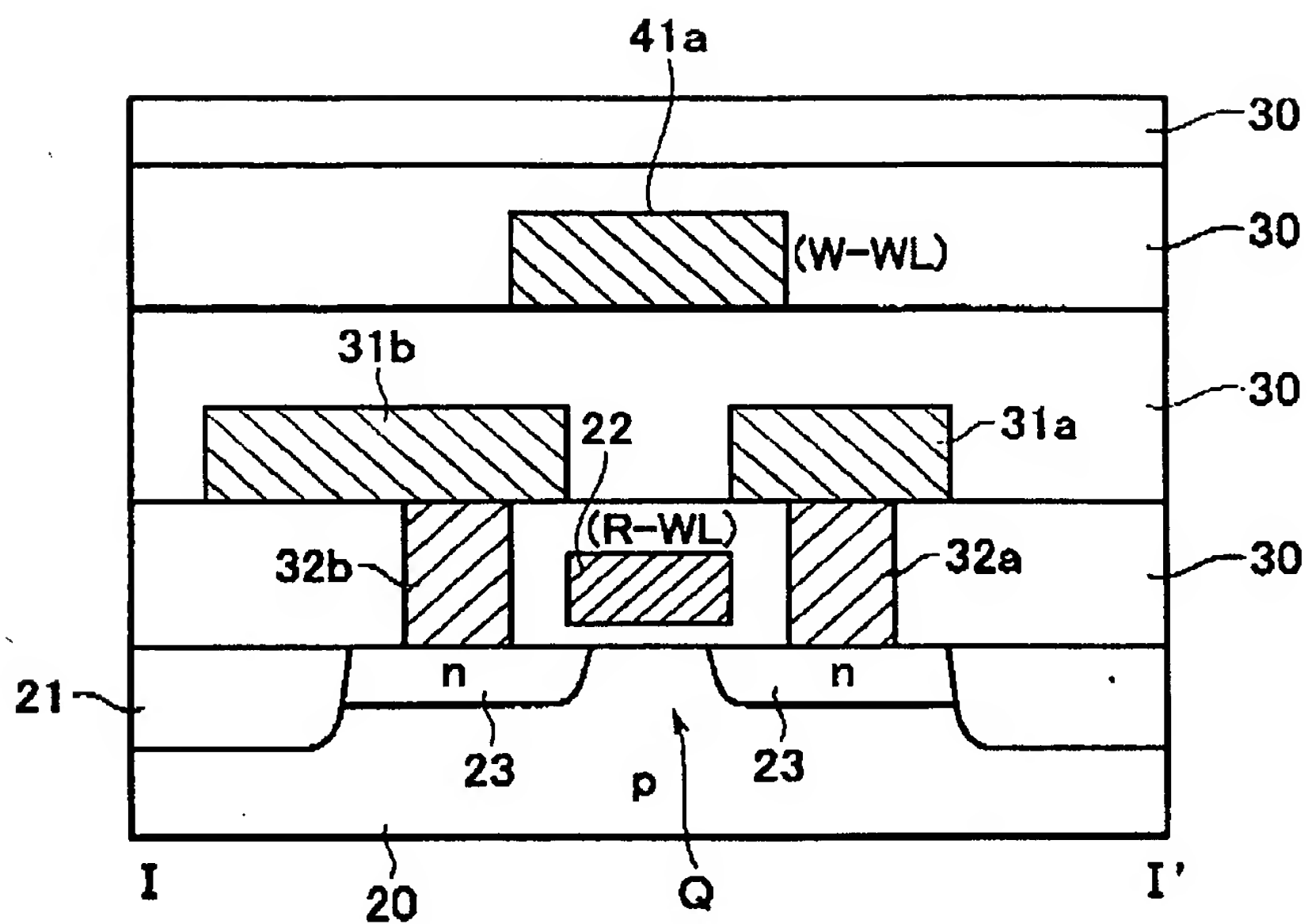


FIG. 6B

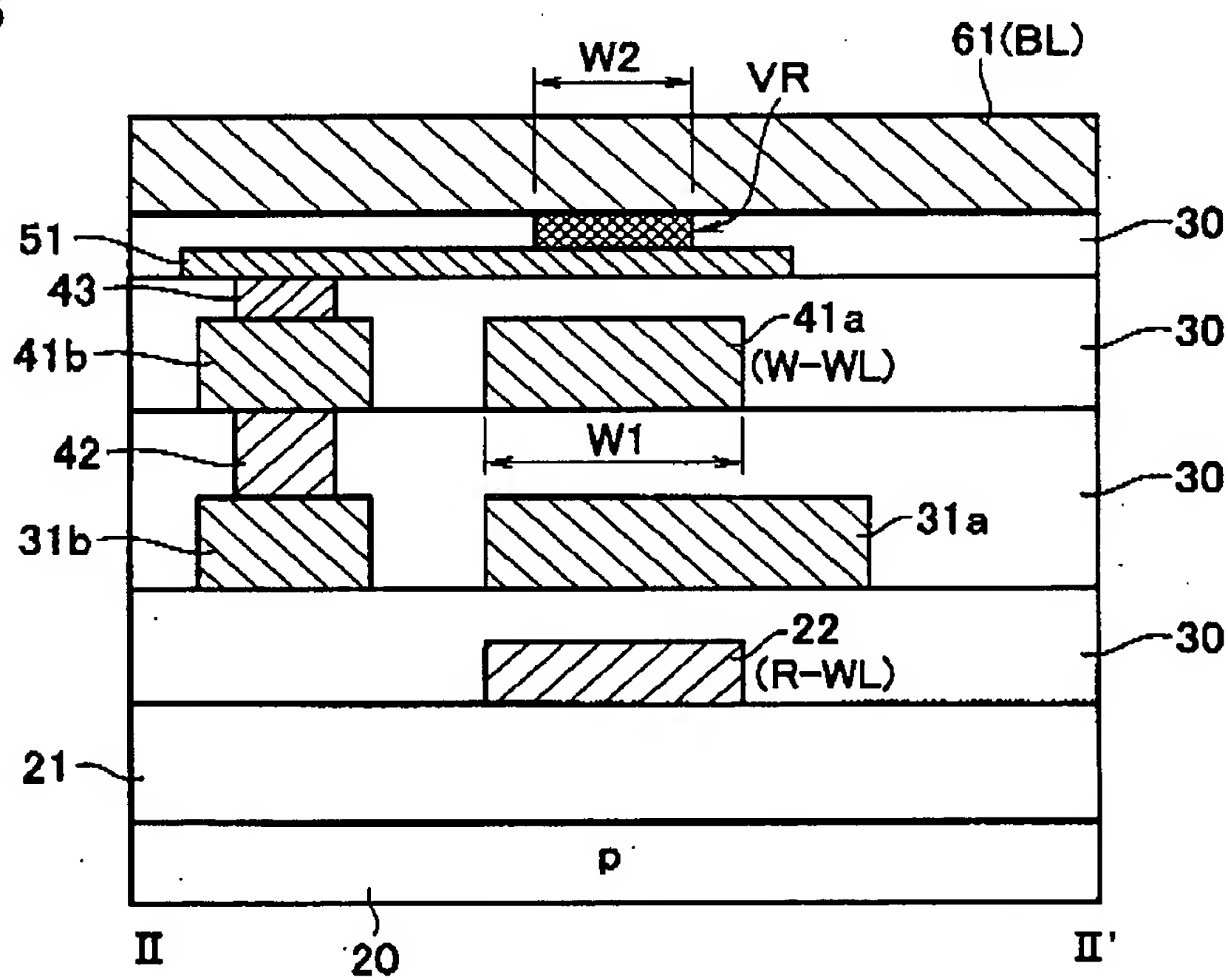


FIG. 7

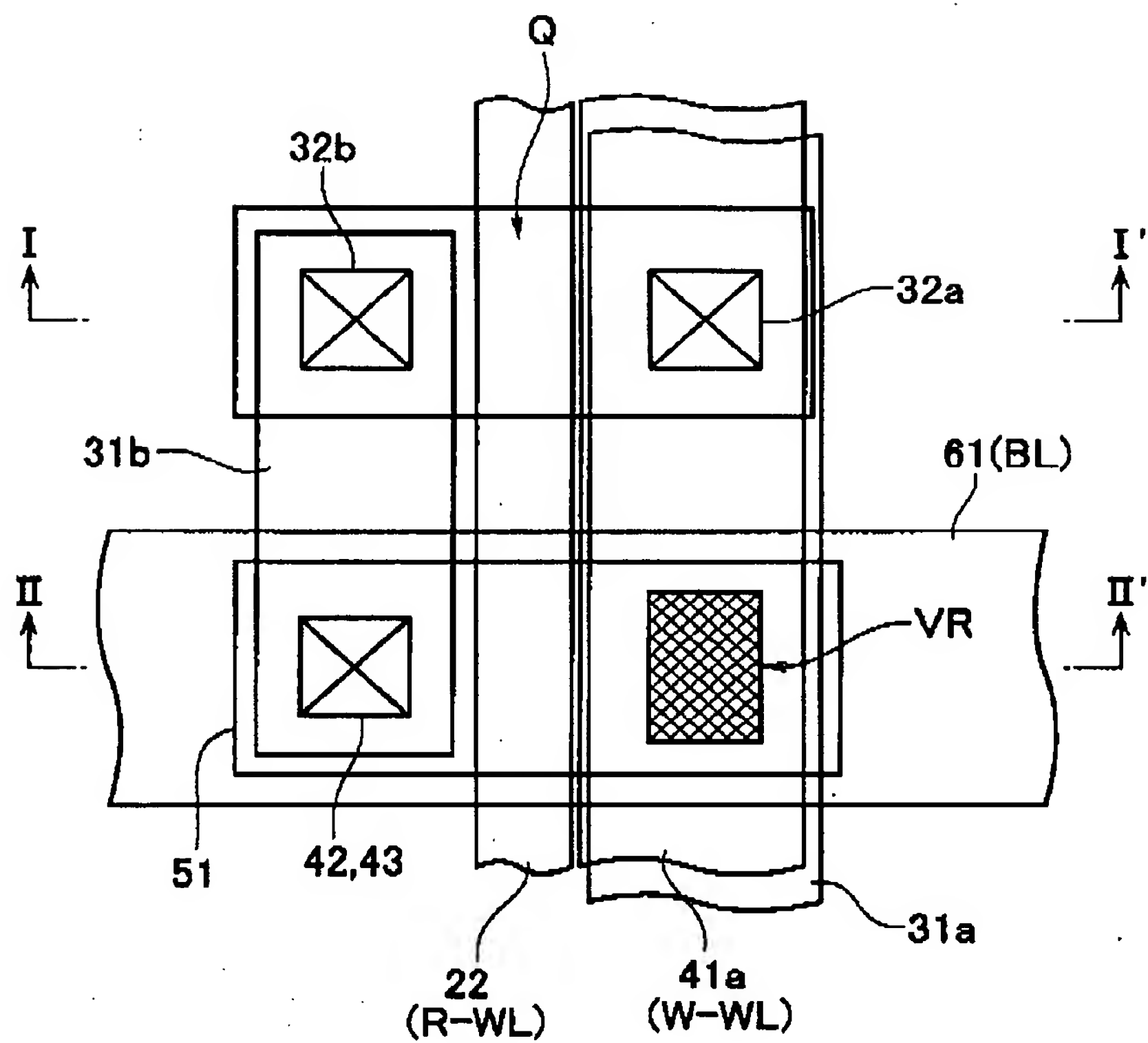


FIG. 8A

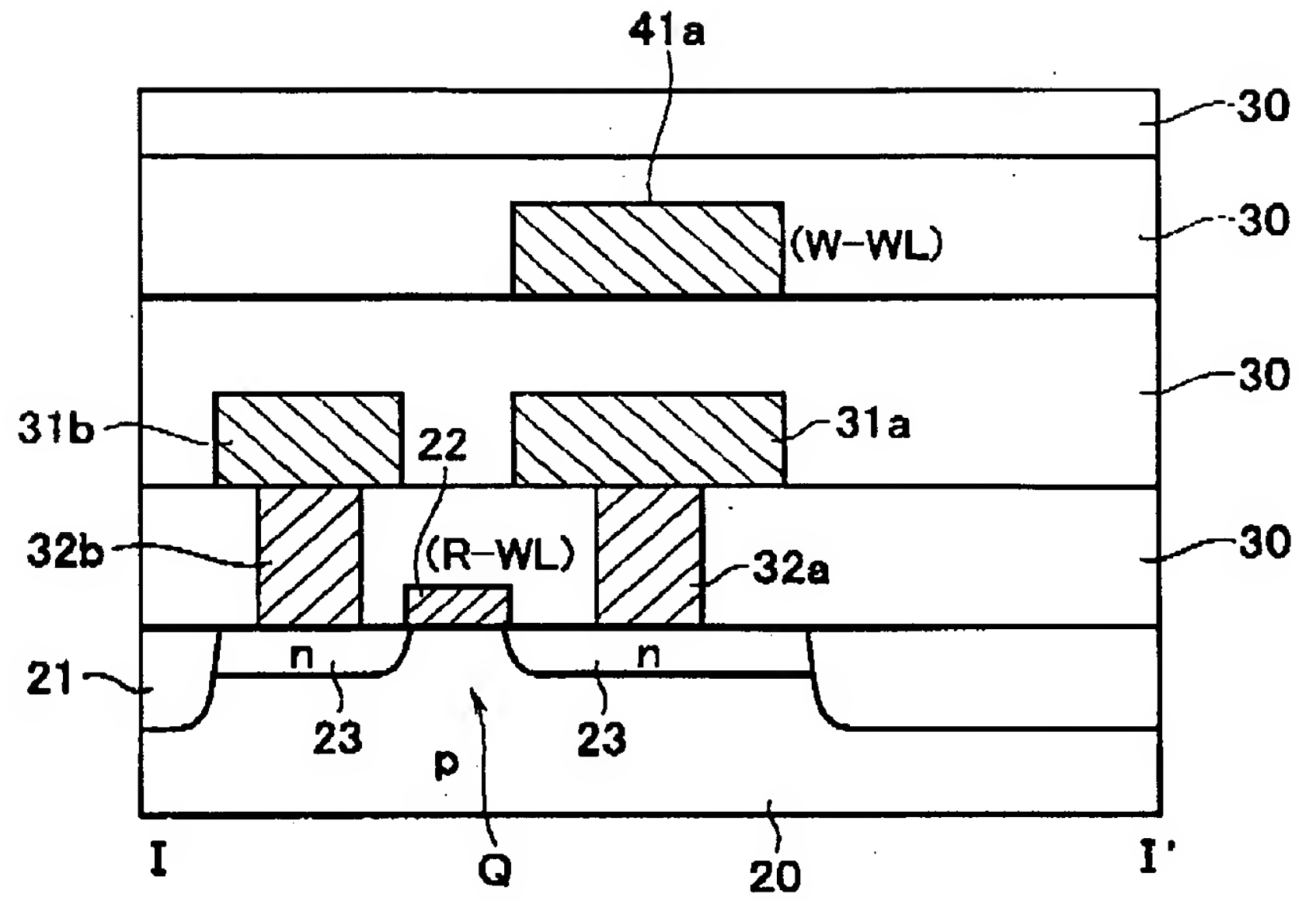


FIG. 8B

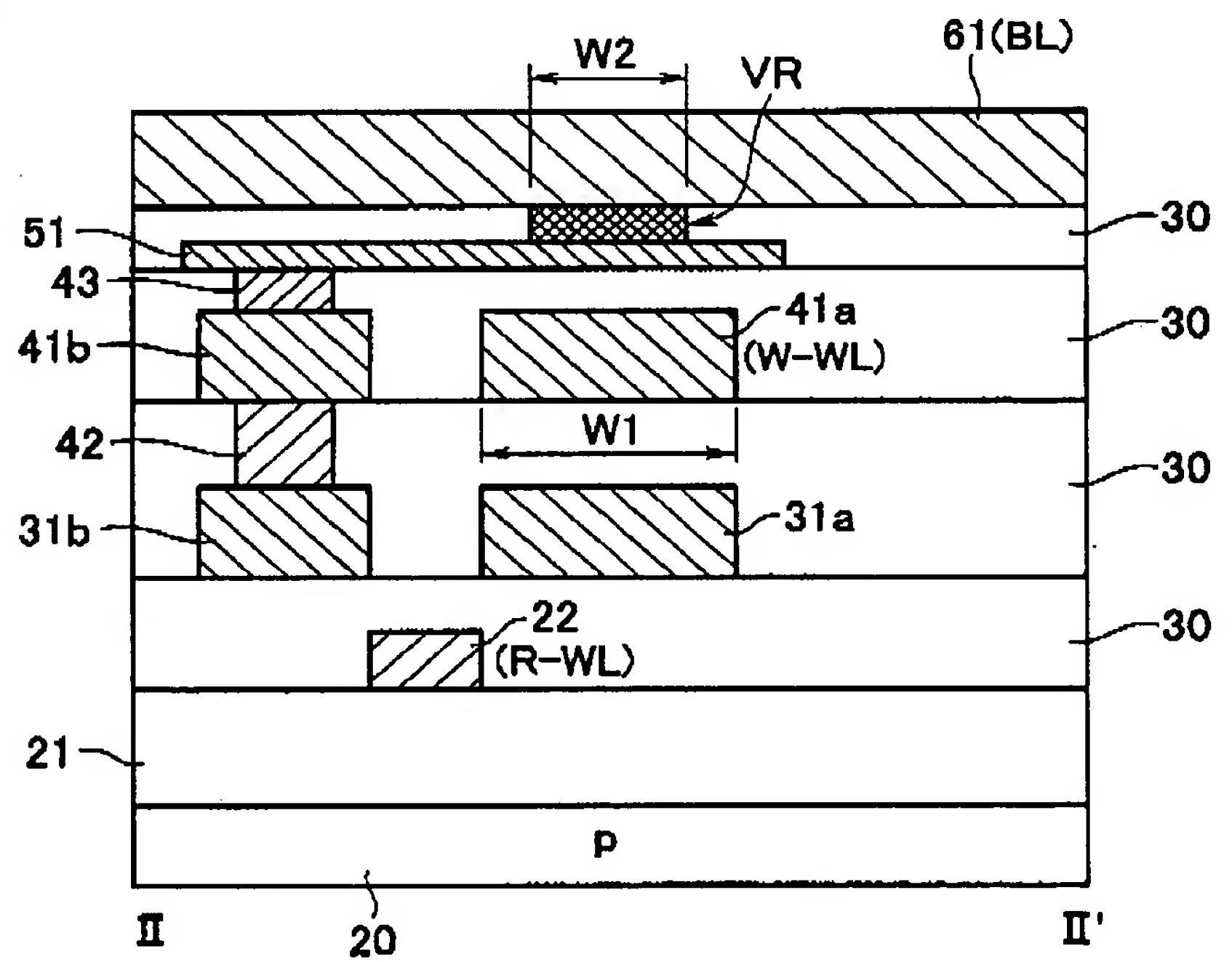




FIG. 9

(PRIOR ART)

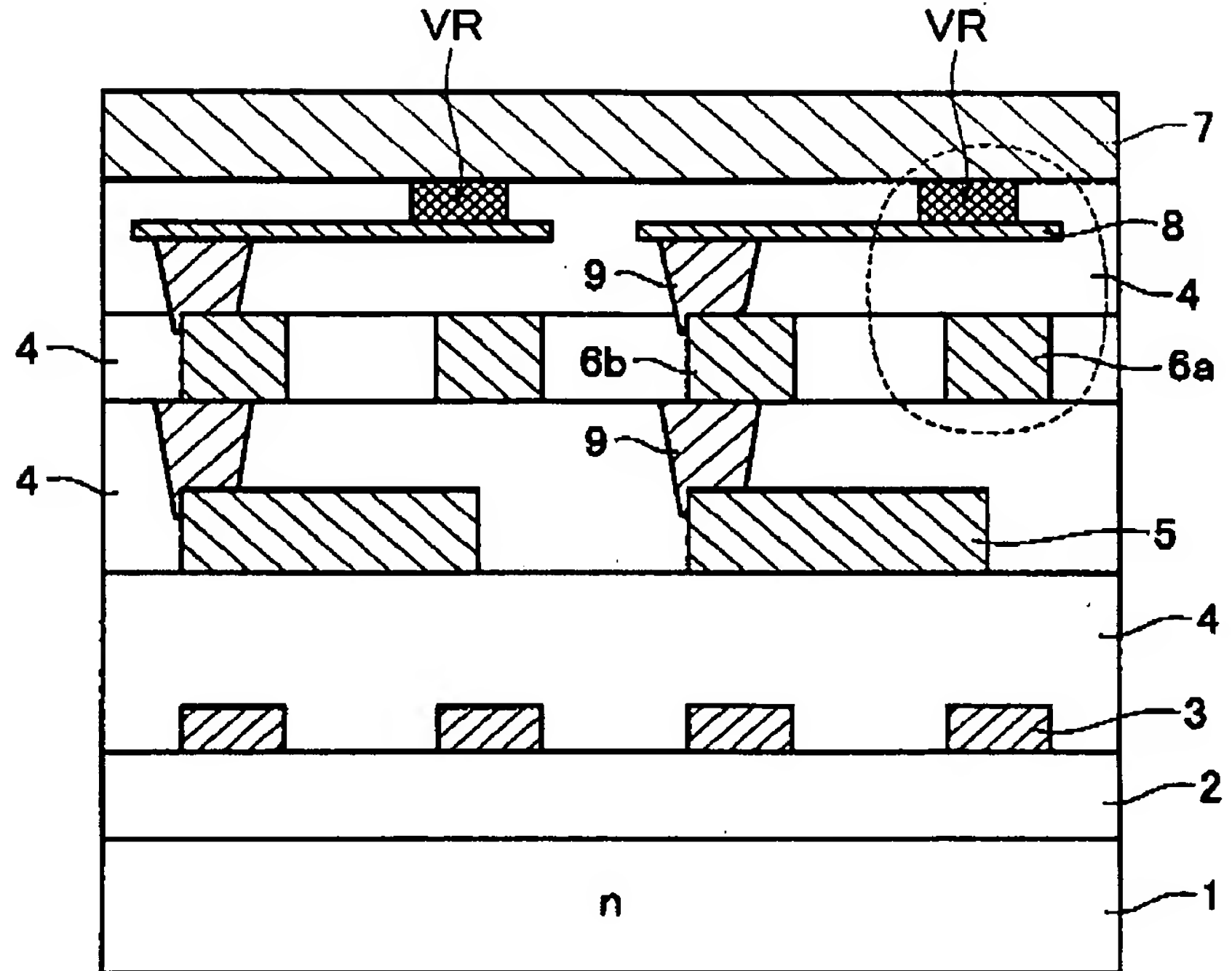


FIG. 10

(PRIOR ART)

